

# 2SB745, 2SB745A

Silicon PNP epitaxial planer type

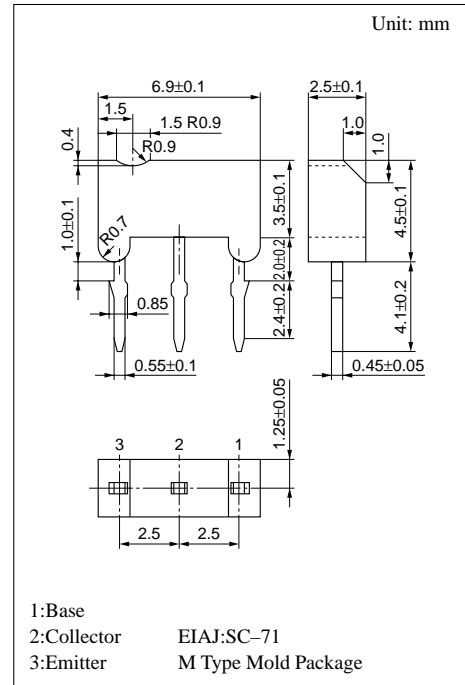
For low-frequency and low-noise amplification  
Complementary to 2SD661 and 2SD661A

## ■ Features

- Low noise voltage NV.
- High forward current transfer ratio  $h_{FE}$ .
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

## ■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	2SB745	-35	V
	2SB745A	-55	
Collector to emitter voltage	2SB745	-35	V
	2SB745A	-55	
Emitter to base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-200	mA
Collector current	$I_C$	-50	mA
Collector power dissipation	$P_C$	400	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C



## ■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CB0}$	$V_{CB} = -10V, I_E = 0$			-100	nA
	$I_{CE0}$	$V_{CE} = -10V, I_B = 0$			-1	μA
Collector to base voltage	$V_{CBO}$	$I_C = -10\mu A, I_E = 0$	-35			V
			-55			
Collector to emitter voltage	$V_{CEO}$	$I_C = -2mA, I_B = 0$	-35			V
			-55			
Emitter to base voltage	$V_{EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	$h_{FE}^*$	$V_{CB} = -5V, I_E = 2mA$	180		700	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.6	V
Base to emitter voltage	$V_{BE}$	$V_{CE} = -1V, I_C = -100mA$		-0.7	-1	V
Transition frequency	$f_T$	$V_{CB} = -5V, I_E = 2mA, f = 200MHz$		150		MHz
Noise voltage	NV	$V_{CE} = -10V, I_C = -1mA, G_v = 80dB$ $R_g = 100k\Omega, \text{Function} = \text{FLAT}$			150	mV

\* $h_{FE}$  Rank classification

Rank	R	S	T
$h_{FE}$	180 ~ 360	260 ~ 520	360 ~ 700

